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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/091,698	03/05/2002	Brian N. Ripley	100202181-1	7441
75	90 10/06/2006		EXAMINER	
HEWLETT-PACKARD COMPANY Intellectual Property Administration			ROJAS, MIDYS	
P.O. Box 27240	-		ART UNIT	PAPER NUMBER
Fort Collins, Co	O 80527-2400		2185	
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Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	
	10/091,698	RIPLEY, BRIAN N.	
Office Action Summary	Examiner	Art Unit	<del></del>
	Midys Rojas	2185	
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet wi	th the correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a repl - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b).	I36(a). In no event, however, may a rely within the statutory minimum of thirt will apply and will expire SIX (6) MON e, cause the application to become AB	eply be timely filed  (30) days will be considered timely.  THS from the mailing date of this communication  ANDONED (35 U.S.C. § 133).	en.
Status			
1) Responsive to communication(s) filed on 30 J	<u>une 20</u> 06.		
2a) This action is <b>FINAL</b> . 2b) ⊠ This	s action is non-final.		
3) Since this application is in condition for allowa closed in accordance with the practice under E			S
Disposition of Claims			
4) Claim(s) 1-14,16-20 and 23-25 is/are pending 4a) Of the above claim(s) is/are withdra 5) Claim(s) is/are allowed. 6) Claim(s) 1-14,16-20 and 23-25 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or	wn from consideration.		
Application Papers			•
9) The specification is objected to by the Examine	er.		
10)⊠ The drawing(s) filed on 05 March 2002 is/are:	a)⊠ accepted or b)☐ obj	ected to by the Examiner.	
Applicant may not request that any objection to the	drawing(s) be held in abeyan	ce. See 37 CFR 1.85(a).	,
Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Ex	•		d).
Priority under 35 U.S.C. § 119	•		
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Bureau	ts have been received.  Its have been received in A rity documents have been	oplication No	
* See the attached detailed Office action for a list	of the certified copies not	received.	•
Attachment(s)			
1) Notice of References Cited (PTO-892)		ummary (PTO-413)	
<ul> <li>Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)</li> <li>Paper No(s)/Mail Date</li> </ul>		)/Mail Date formal Patent Application (PTO-152)	

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### **DETAILED ACTION**

## Response to Arguments

Applicant's arguments filed on June 30<sup>th</sup>, 2006 have been considered but are not persuasive.

Applicant argues that neither Lee et al. or Chan et al. disclose receiving "a number of bits corresponding to the width of the variable width memory locations and the width of a variable width register". However, Chan et al. discloses a variable cell size circuit 200 that defines the number of bytes (number of bits that will be received in a memory location) per cell for an access operation to a cell (Col. 5, lines 2-18).

### Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-14, 16-20, and 23-25 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lee et al. (2003/0158995) in view of Chan et al. (6,230,249).

Regarding Claim 1, Lee discloses a variable width memory system comprising (DRAM control with adjustable page size):

- a bus for communicating information (Figure 1, exemplary system, buses 160, 170);
- a plurality of memory locations coupled to said bus (memory locations of memory 140), said plurality of variable width memory locations store information (DRAM access, Abstract,

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wherein storing is an accesses), wherein said plurality of variable width memory locations receive a number of bits corresponding to the width of the variable memory locations (determining adjustable page portion, Claim 1); and a controller coupled to said bus 410 (Figure 4), said controller directs access to said plurality of variable width memory locations being accessed (page 2, paragraphs 18 and 19). Being that the memory has variable widths (page size), the number of widths accessed depends of the current width of the memory location accessed. Additionally, since the page width is determined for each access, all memory pages do not have to have the same width.

Lee does not teach the variable width memory locations being single cell memory locations and receiving a number of bits in the single cell memory locations corresponding to the width of a variable width register. Chan et al. discloses a system with a FIFO memory device containing programmable variable cell sizes (see Abstract and Col. 2, line 65- Col. 3, line 14). The system of Chan teaches a variable cell size circuit 200 that defines the number of bytes (number of bits that will be received in a memory location) per cell for an access operation to a cell (Col. 5, lines 2-18). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the system of Lee to include the variable width memory cells of Chan as well as the variable cell size circuit and further more, apply its variable memory location control method to the new variable memory cells since variable memory cells provides for a more flexible memory device that may be suited for more applications (see Chan Col. 1, lines 47-55 for motivation).

Regarding Claim 2, Lee in view of Chan discloses variable width memory locations 420 included on a single memory substrate (see Figure 4).

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Regarding Claim 3, the memory of Lee can be implemented a DRAM (abstract).

Regarding Claims 4-5, the memory locations of Lee in view of Chan have individual addresses (memory row address, memory column strobe, Page 2, paragraph 19) and therefore, are identified by unique internal identifiers. In making access requests, the addresses are used by the controller. Additionally, such addresses are part of a mapping system used at the time of access implemented in the memory controller 410.

Regarding Claim 6, in the system of Lee in view of Chan, two memory locations could have the same width (page size) depending on the parameters being used and in what the page sizes are determined to be in step 520 (Figure 5, and paragraphs 0025-0026).

Regarding Claim 7, Lee in view of Chan discloses variably configuring the width (page size) of the memory in order to achieve a reduction delay by increasing page hit rate (processor operations) thus decreasing power consumption (paragraph 0008).

Regarding Claim 8 and 14, Lee et al. discloses a variable width memory (Fig. 1, 140) comprising receiving a register indicator corresponding to a register (internal address provided from the requester); accessing a memory cell (memory controller multiplexes row and column address to system memory) based on said register indicator, wherein said memory cell is allocated a storage size correlating to the bit capacity of said register (determine page size, Figure 5); and transferring information between said memory cell and another component (data is transferred between memory controller and system memory 420, paragraph 0019), wherein said information includes the same number of bits as said bit capacity, and varying the bit capacity on a per access basis to the memory cell automatically (Figure 5). Being that the memory has variable widths (page size), the number of widths accessed depends of the current

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width of the memory location accessed. Additionally, since the page width is determined for each access, all memory pages do not have to have the same width.

Lee does not teach the variable width memory locations being single cell memory locations and receiving a number of bits in the single cell memory locations corresponding to the width of a register. Chan et al. discloses a system with a FIFO memory device containing programmable variable cell sizes (see Abstract and Col. 2, line 65- Col. 3, line 14). The system of Chan teaches a variable cell size circuit 200 that defines the number of bytes (number of bits that will be received in a memory location) per cell for an access operation to a cell (Col. 5, lines 2-18). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the system of Lee to include the variable width memory cells of Chan as well as the variable cell size circuit and further more, apply its variable memory location control method to the new variable memory cells since variable memory cells provides for a more flexible memory device that may be suited for more applications (see Chan Col. 1, lines 47-55 for motivation).

Regarding Claims 9, the register indicator (memory address) is received from a processor (requester). Page 2, paragraph 0018.

Regarding Claim 10, the bit capacity is determined (Figure 5) by processing criteria (input from requester) associated with a processor.

Regarding Claim 11, the data being transferred (see Figure 4) is in the form of a packet wherein packets are a group of bits or bytes of information.

Regarding Claim 12, the information being transferred to and from the memory also includes information such as column address strobe, row address strobe, and write enable

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(paragraph 0019). These commands are associated with certain fields in the memory and participate in the performance of accessing functions for completing such commands.

Regarding Claim 13, the information being transferred that is associated with certain fields (row and column address information) is sequentially received and taken in by the memory 420 (see Figure 4).

Regarding Claim 20, Lee et al. discloses a variable memory width assignment method (Figure 5) comprising analyzing a data block configuration specification (as part of determining process 520, Figure 5); identifying bits in a portion of said block of data while variably configuring the width (page size) of the memory in order to achieve a reduction delay by increasing page hit rate (processor operations) thus decreasing power consumption (paragraph 0008); and assigning a memory location width equal to said number of bits in said portion of said block of data (produce an adjustable page portion for prior access... Page 3, paragraph 0023), the data being transferred (see Figure 4) is in the form of a packet wherein packets are a group of bits or bytes of information; this information also includes column address strobe, row address strobe, and write enable (paragraph 0019). These commands are associated with certain fields in the memory and participate in the performance of accessing functions for completing such commands; they are sequentially received and taken in by the memory 420 (see Figure 4).

Being that the memory has variable widths (page size), the number of widths accessed depends of the current width of the memory location accessed. Additionally, since the page width is determined for each access, all memory pages do not have to have the same width.

Lee does not teach the variable width memory locations being single cell memory locations and receiving a number of bits in the single cell memory locations corresponding to the

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width of a variable width register. Chan et al. discloses a system with a FIFO memory device containing programmable variable cell sizes (see Abstract and Col. 2, line 65- Col. 3, line 14). The system of Chan teaches a variable cell size circuit 200 that defines the number of bytes (number of bits that will be received in a memory location) per cell for an access operation to a cell (Col. 5, lines 2-18). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the system of Lee to include the variable width memory cells of Chan as well as the variable cell size circuit and further more, apply its variable memory location control method to the new variable memory cells since variable memory cells provides for a more flexible memory device that may be suited for more applications (see Chan Col. 1, lines 47-55 for motivation).

Regarding Claims 16-18, as in all memories, the variable page size memory of Lee et al. has many memory locations uniquely identified by memory addresses, which could be known as external identifiers (paragraph 0018) and these are used in accessing the adjustable memory pages (locations of various widths, paragraph 0010).

Regarding Claim 19, Lee et al. discloses an adjustable page size memory system, which arranges incoming bits in a contiguous manner during the write operation (paragraph 0019).

Regarding Claim 23, Lee et al. discloses a variable width memory (adjustable page size) assignment system (Abstract) comprising a means for communicating memory location identifiers (internal address provided by the requester); a means for storing information in a uniquely identifiable different width memory locations corresponding to said memory location identifiers (RAS# and CAS# are used to access adjustable pages within memory 420, Figure 4. Paragraphs 0010 and 0018-0020), wherein said means for storing said information returns a

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number of bits equal to the width of one of said uniquely identifiable different width memory locations in response to a read request (read request, paragraph 0019); and a means for managing a connection with said uniquely identifiable different width memory locations (DRAM cotroller 410), wherein said means for managing said connection supervises writing and reading of information to and from said uniquely identifiable different width memory location. Being that the memory has variable widths (page size), the number of widths accessed depends of the current width of the memory location accessed. Additionally, since the page width is determined for each access, all memory pages do not have to have the same width.

Lee does not teach the variable width memory locations being single cell memory locations and receiving a number of bits in the single cell memory locations corresponding to the width of a variable width register. Chan et al. discloses a system with a FIFO memory device containing programmable variable cell sizes (see Abstract and Col. 2, line 65- Col. 3, line 14). The system of Chan teaches a variable cell size circuit 200 that defines the number of bytes (number of bits that will be received in a memory location) per cell for an access operation to a cell (Col. 5, lines 2-18). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the system of Lee to include the variable width memory cells of Chan as well as the variable cell size circuit and further more, apply its variable memory location control method to the new variable memory cells since variable memory cells provides for a more flexible memory device that may be suited for more applications (see Chan Col. 1, lines 47-55 for motivation).

Regarding Claim 24, Lee in view of Chan discloses the variable width memory assignment system wherein said means for managing said connection (memory controller 410)

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includes a means for tracking a correspondence between said uniquely identifiable variable memory widths and register identifiers (asserts RAS# and CAS# signals from internal address provided by requester, paragraphs 0018-0019).

Regarding Claim 25, Lee in view of Chan discloses the variable width memory assignment system wherein said register identifiers are provided by a means for processing said information (internal address provided by requester, paragraph 0018).

### **Conclusion**

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Midys Rojas whose telephone number is (571) 272-4207. The examiner can normally be reached on M-F 5:30am - 4:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Sanjiv Shah can be reached on (571) 272-4098. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Midys Rojas

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MR

September 29<sup>th</sup>, 2006

SANJIV SHAH
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2100